

Monolithic Active Pixel Sensor for a “Tera-Pixel” ECAL at the ILC

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Introduction

SiW ECAL for ILC

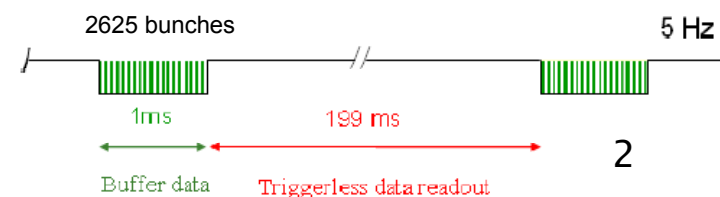
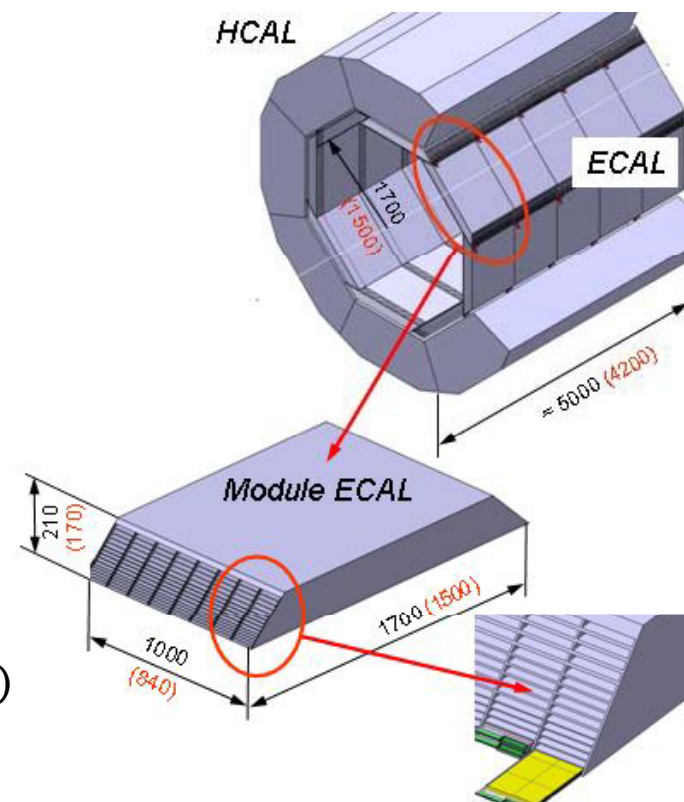
- 30 layers silicon & tungsten
- Prove Monolithic Active Pixel Sensor (MAPS) as a viable solution for the silicon!

Machine operation

- 2ms “bunch train” of events
- 198ms between bunch trains for readout

Sensor Specification

- Sensitive to MIP signal
- Small pixels determine “hit” status (binary readout)
- Store timestamp & location of “hits”
- Target noise rate 10^{-6}
- Design to hold data for 8k bunch crossings before readout
- Minimum “dead space”



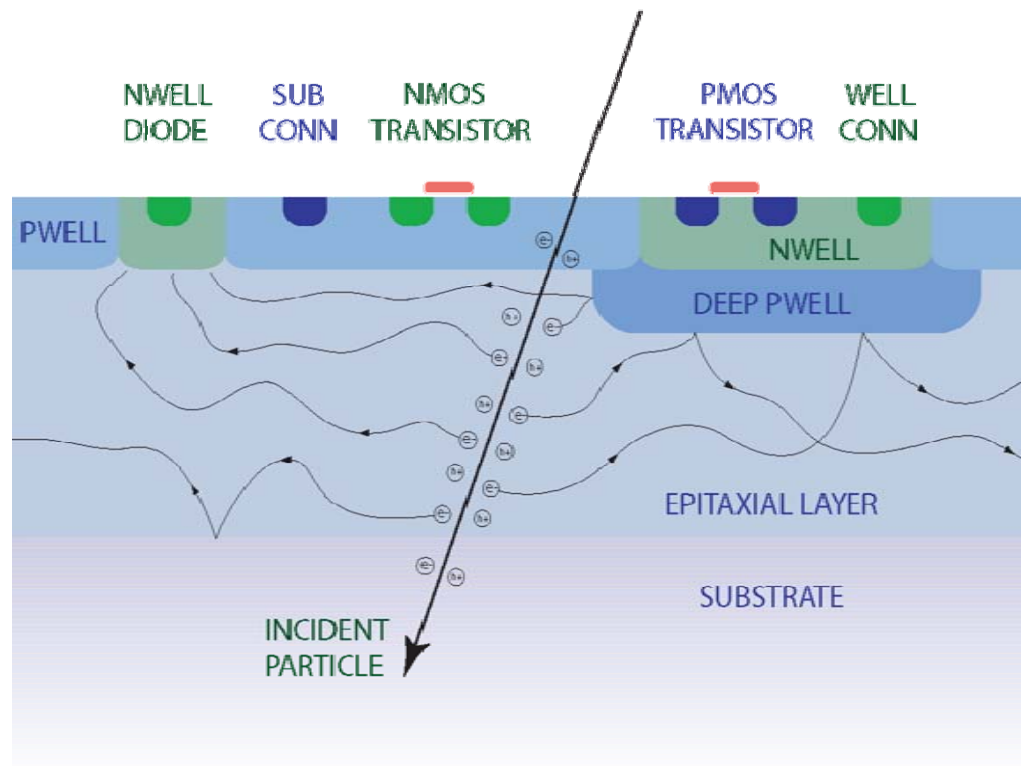


INMAPS Process

- Standard 0.18 micron CMOS

Used in our sensor

- 6 metal layers
- Analog & Digital @ 1.8v & 3.3v
- 12 micron epitaxial layer



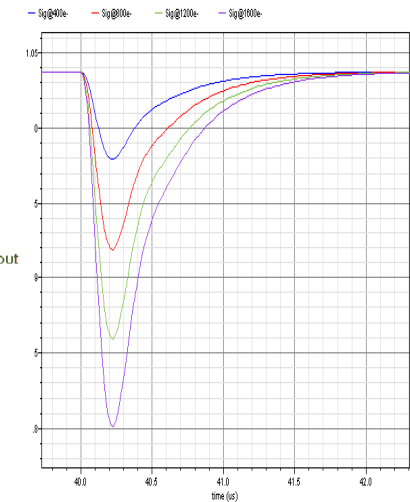
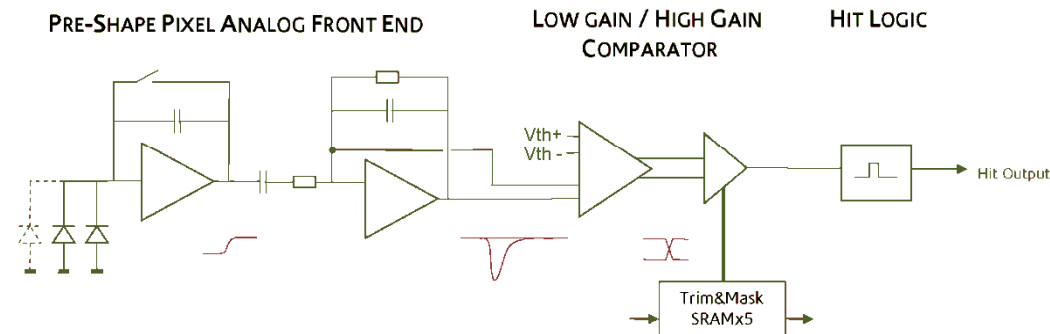
- Additional module: **Deep P-Well**
 - Developed specifically for this project
 - Added beneath all active circuits in the pixel
 - Should reflect charge, preventing unwanted loss in charge collection efficiency
- Device simulations show conservation of charge
- Test chip processing variants
 - Sample parts were manufactured with/without deep p-well for comparison



Pixel Architectures

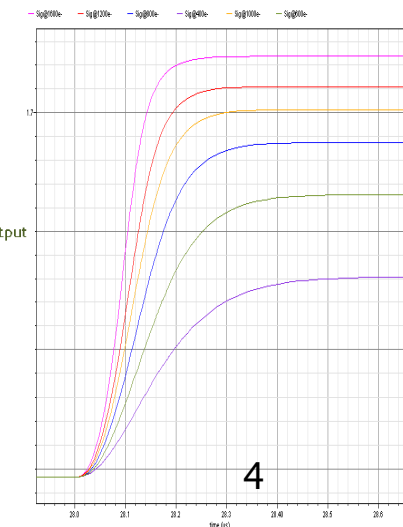
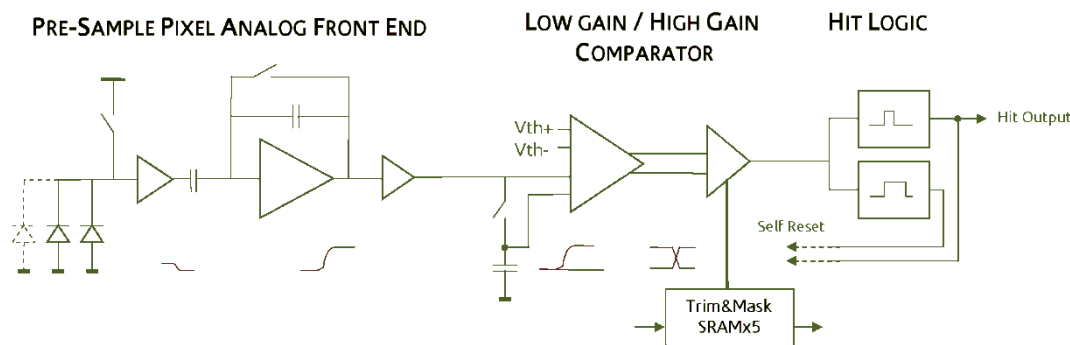
preShape

- Gain $94\mu\text{V}/e$
- Noise $23e^-$
- Power $8.9\mu\text{W}$
- 150ns “hit” pulse wired to row logic
- Shaped pulses return to baseline



preSample

- Gain $440\mu\text{V}/e$
- Noise $22e^-$
- Power $9.7\mu\text{W}$
- 150ns “hit” pulse wired to row logic
- Per-pixel self-reset logic





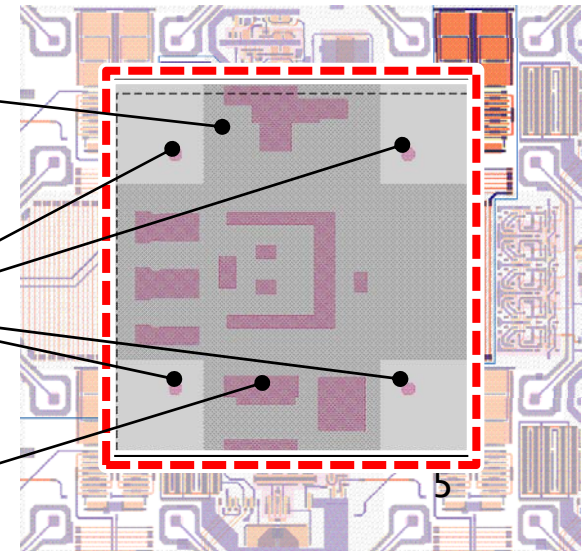
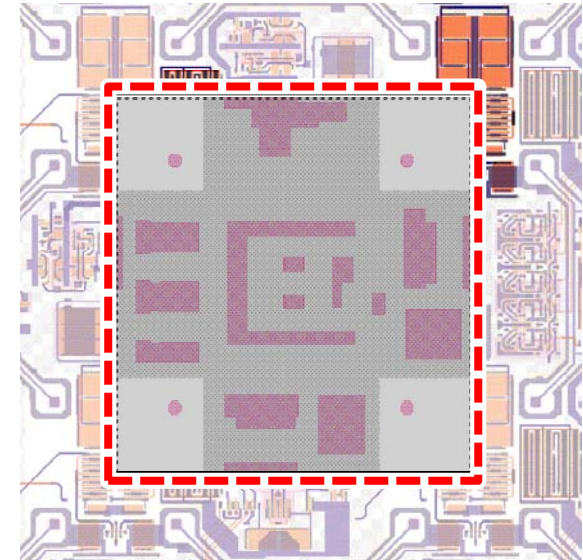
Pixel Layouts

preSample Pixel

- 4 diodes
- 189 transistors
- 34 unit capacitors
- Configuration SRAM
 - Mask
 - Comparator trim (4 bits)
- 2 variants: subtle changes to capacitors

preShape Pixel

- 4 diodes
- 160 transistors
- 27 unit capacitors
- 1 resistor (4Mohm)
- Configuration SRAM
 - Mask
 - Comparator trim (4 bits)
- 2 variants: subtle changes to capacitors



Deep p-well

Diodes

*Circuit
N-Wells*

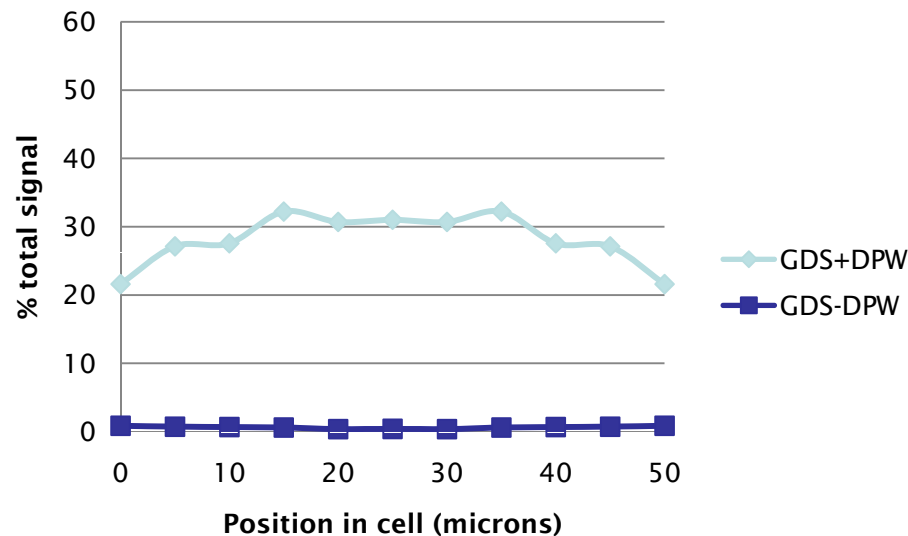
5

Device Simulations

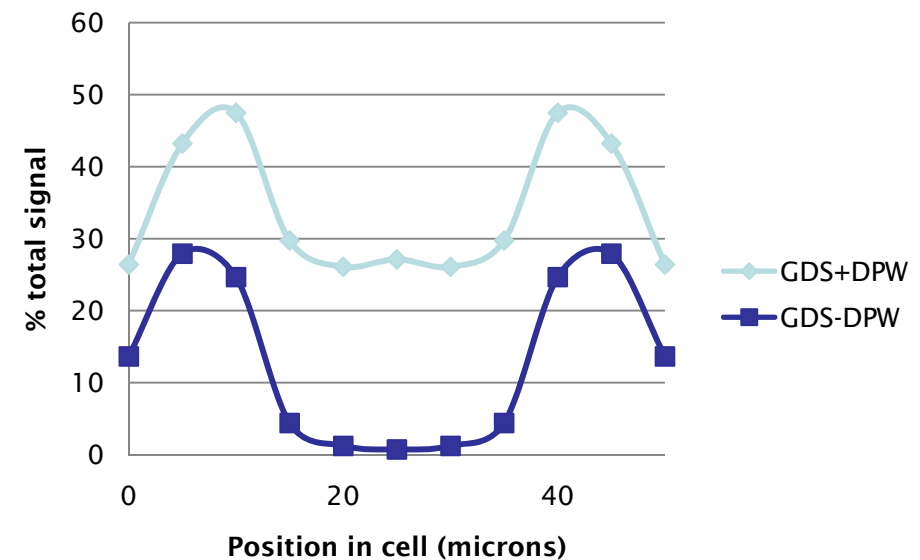
TCAD model of pixel substrate

- Response of each diode recorded for a simulated point charge deposit at different locations
 - Charge collected
 - Collection time

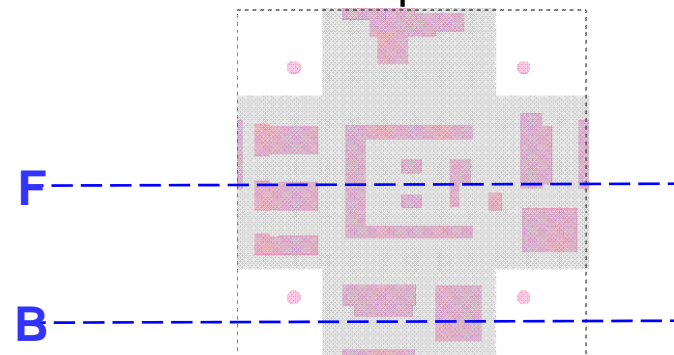
Profile F; through cell



Profile B; through cell



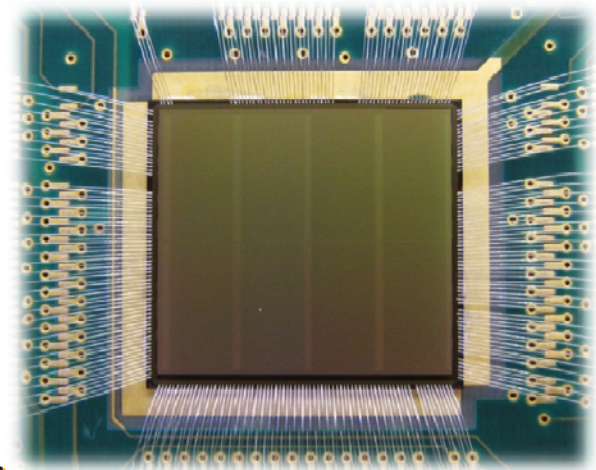
Pixel profiles





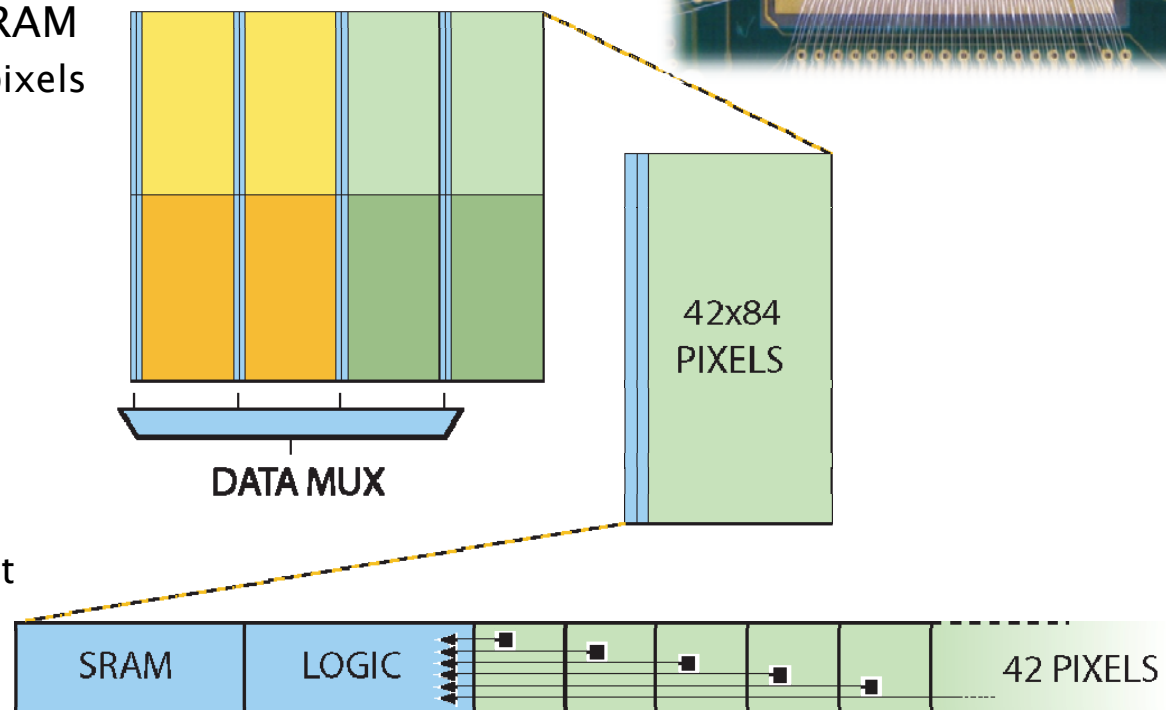
Test Chip Architecture

- 8.2 million transistors
- 28224 pixels; 50 microns; 4 **variants**
- Sensitive area 79.4mm²
 - of which 11.1% “dead” (logic)



- Four columns of logic + SRAM
 - Logic columns serve 42 pixels
 - Record hit locations & timestamps
 - Local SRAM

- Data readout
 - Slow (<5Mhz)
 - Current sense amplifiers
 - Column multiplex
 - 30 bit parallel data output



Sensor Testing: Overview

Test pixels

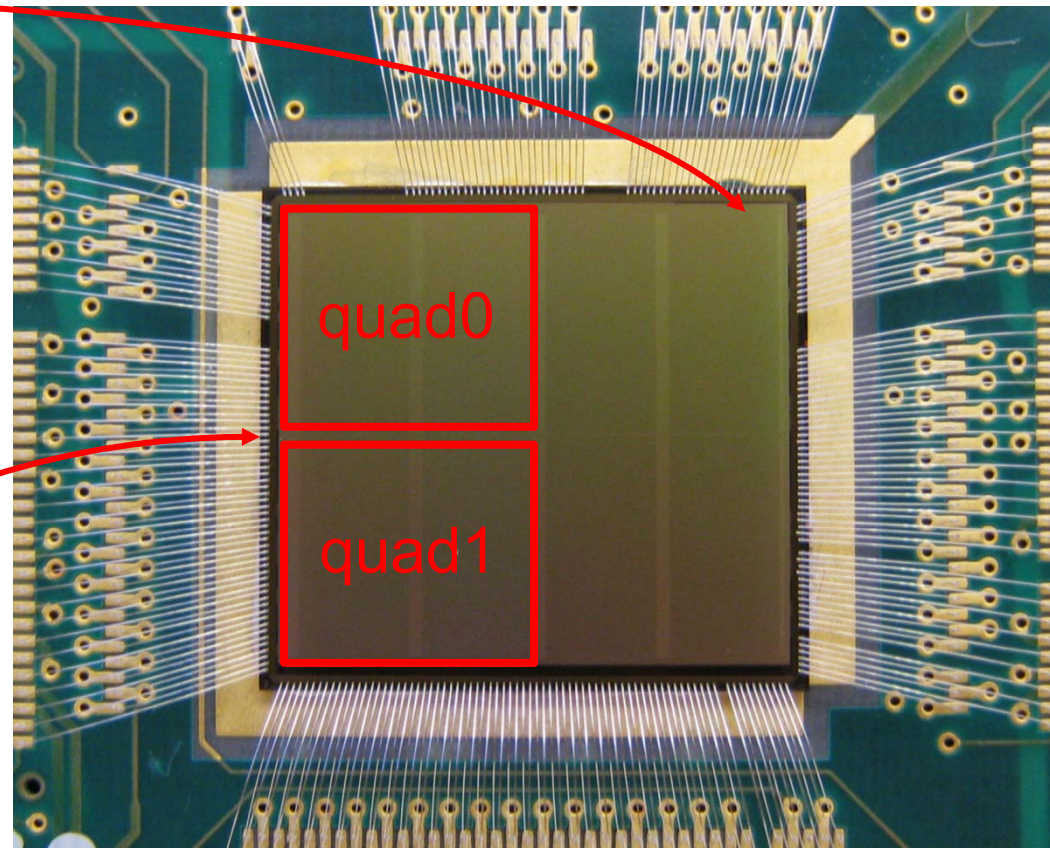
- preSample pixel variant
- Analog output nodes
- Fe55 stimulus
- IR laser stimulus

Single pixel in array

- Per pixel masks
- Fe55 stimulus
- Laser Stimulus

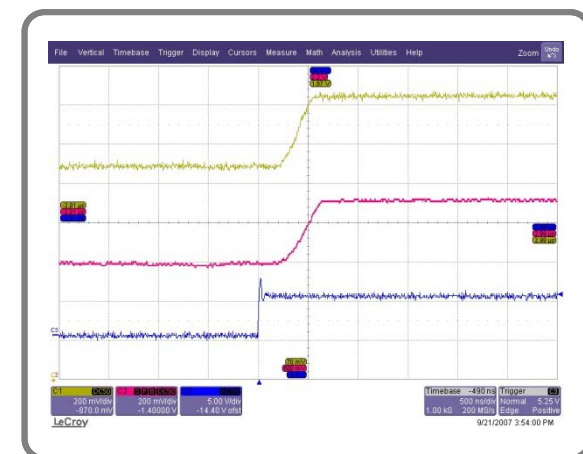
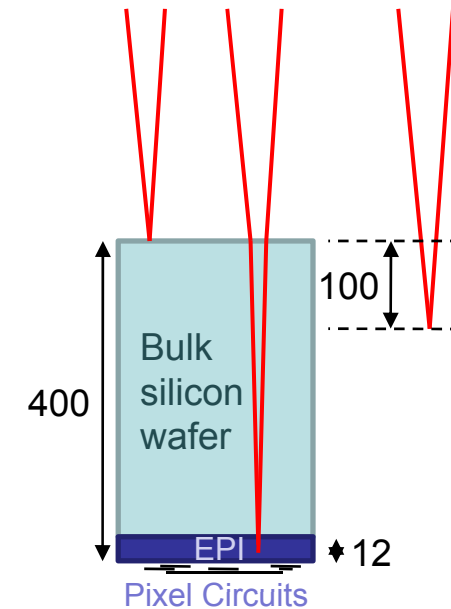
Full pixel array

- preShape (quad0/1)
- Pedestals & trim adjustment
- Gain uniformity
- Crosstalk
- Beam test



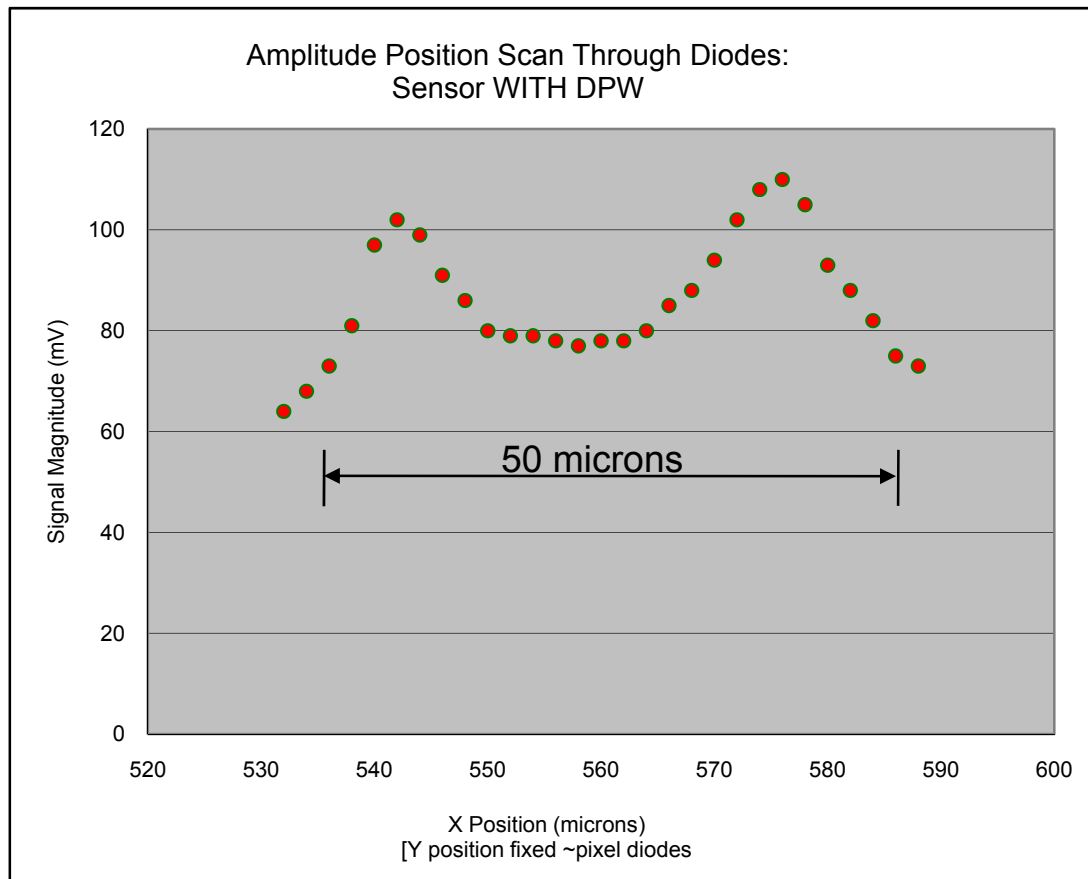
Test pixels: Laser Stimulus

- 1064nm pulsed laser
- 2x2 μ m square area of illumination at focal point
 - Simulates point-charge deposit in pixel
- Illuminate back of sensor
- Silicon is \sim transparent at this λ
- Adjust focus to hit the EPI layer
 - Account for refractive index!
- Scan XY position to 1 μ m accuracy
- Test pixels & laser run asynchronously
- Oscilloscope triggered by laser sync pulse shows analog response from test pixel
- Measure (histogram)
 - Amplitude
 - Time delay
 - = (System Delay) + (charge collection)



Test pixels: Laser Stimulus

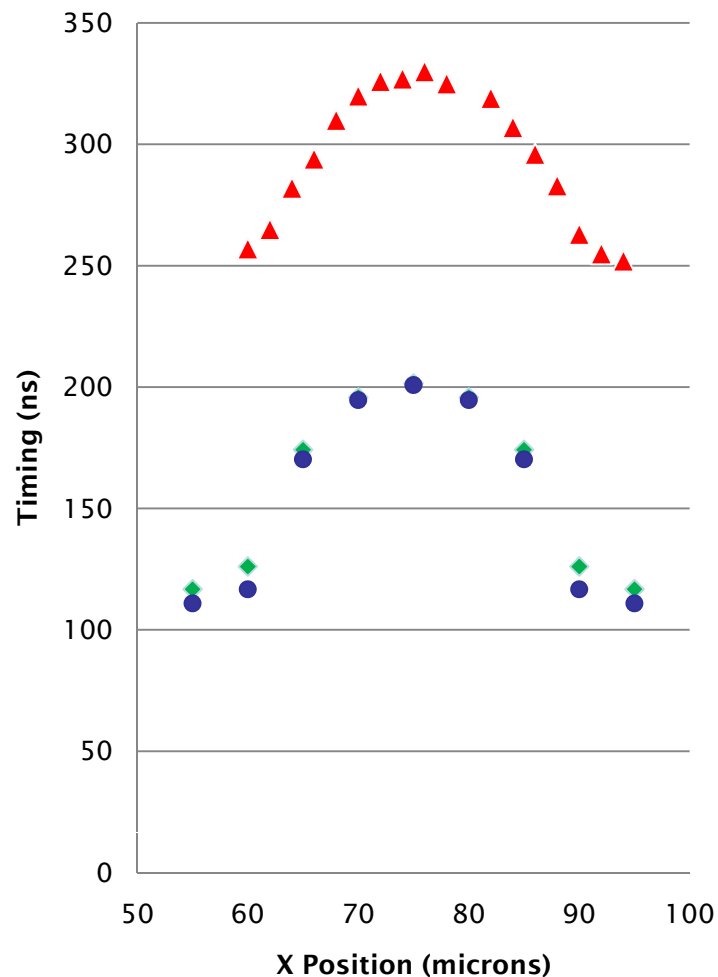
- Optimised Focus
- 2x2um spot, 2um steps
- Profile through 2 diodes in test pixel



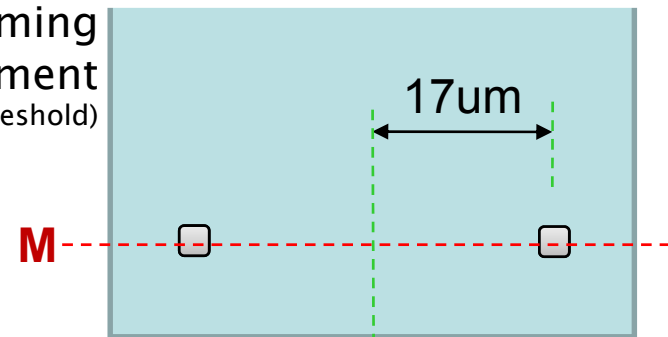
- Automated laser profile of full test pixel area begins...
 - With/without DPW
 - Different depths epi

Test pixels: Laser Stimulus

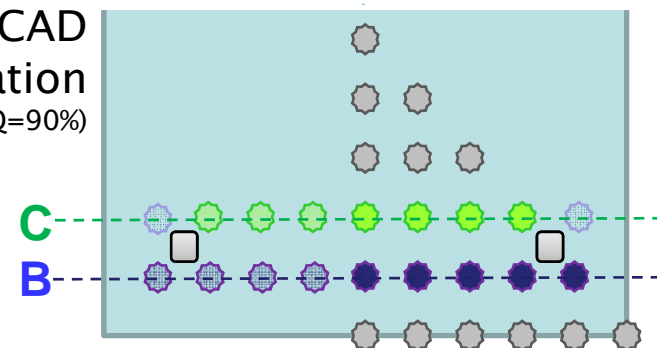
Charge collection time: Measurements vs Simulation



Timing
measurement
(30mV threshold)



TCAD
Simulation
(Q=90%)



Evaluating single pixel performance

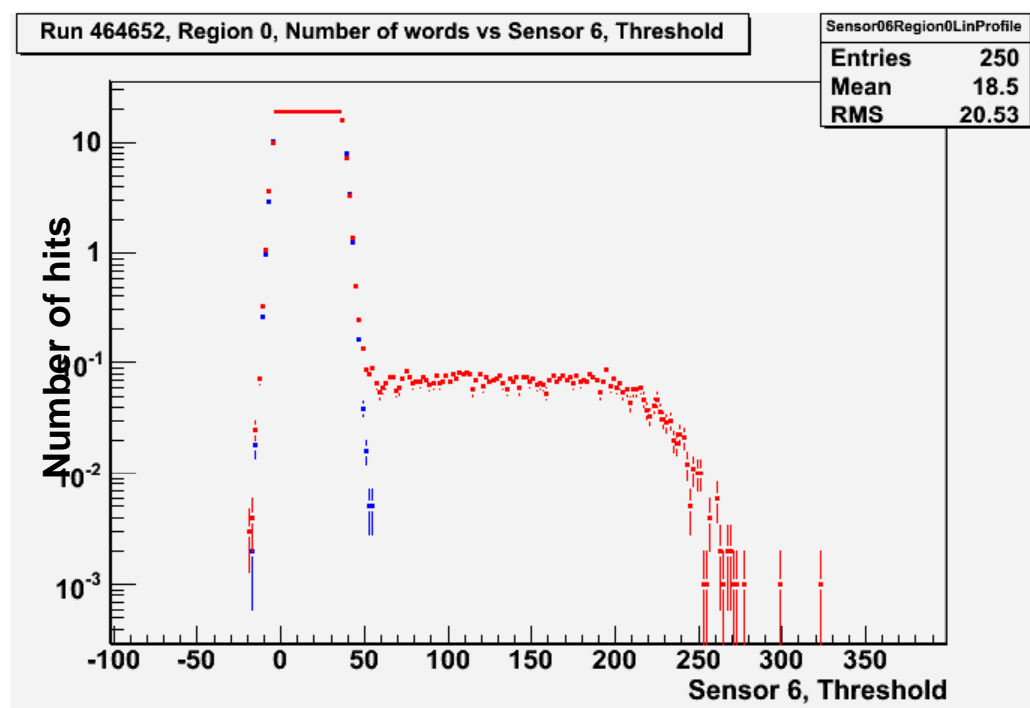
- Binary readout from pixels in the array

- Can mask individual pixels

- Evaluated with a threshold scan...

Single active pixel
with/without laser firing

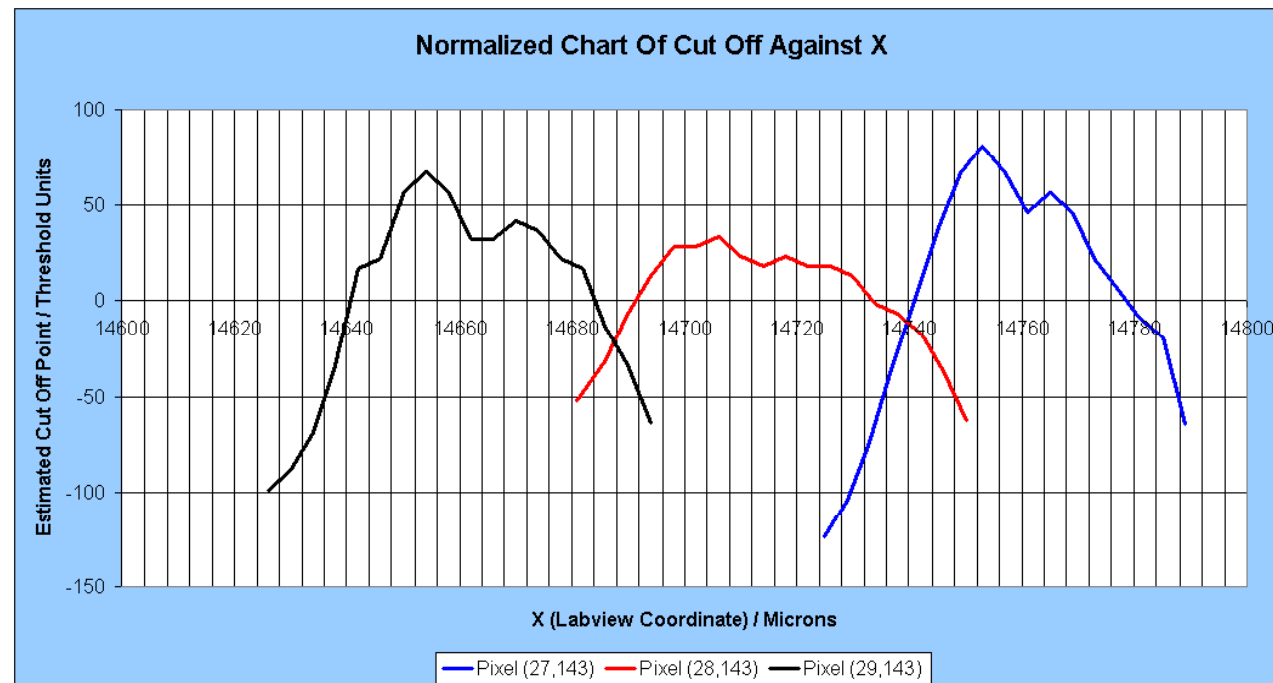
- Record #hits for a given threshold setting
- 1 threshold unit $\sim 0.4\text{mV}$
- Low thresholds \rightarrow noise hits
- Max #hits defined by memory limit ($=19$ per row)
- Comparator is edge-triggered
 - Very small or negative thresholds don't trigger comparator
- Signal should generate hits at higher thresholds than the noise
- No hits expected for very high thresholds





Single Pixel in Array: Laser/Alignment

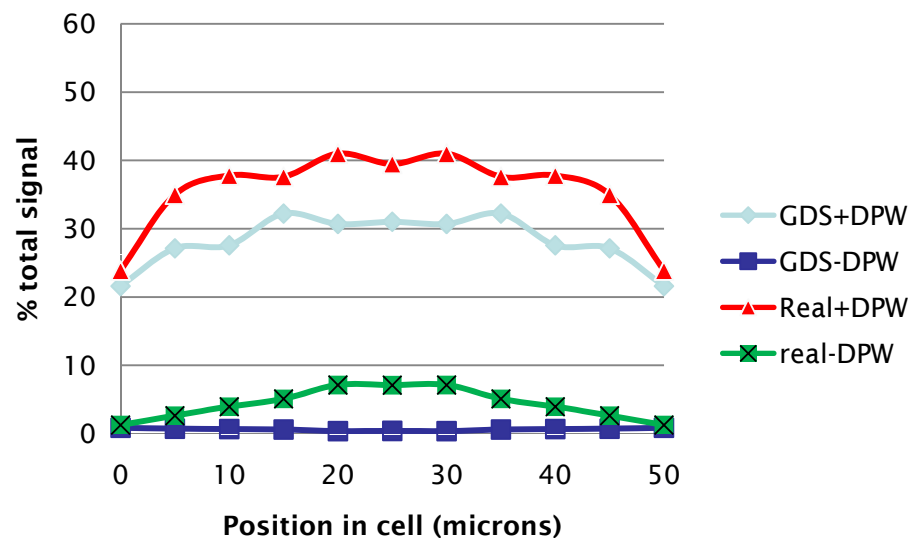
- Use laser for alignment
 - Back of sensor has no features for orientation
 - Mounting is not necessarily square to $<1\mu\text{m}$
 - Laser position scans in X & Y
 - Threshold scan technique
 - Estimate signal magnitude from drop-off



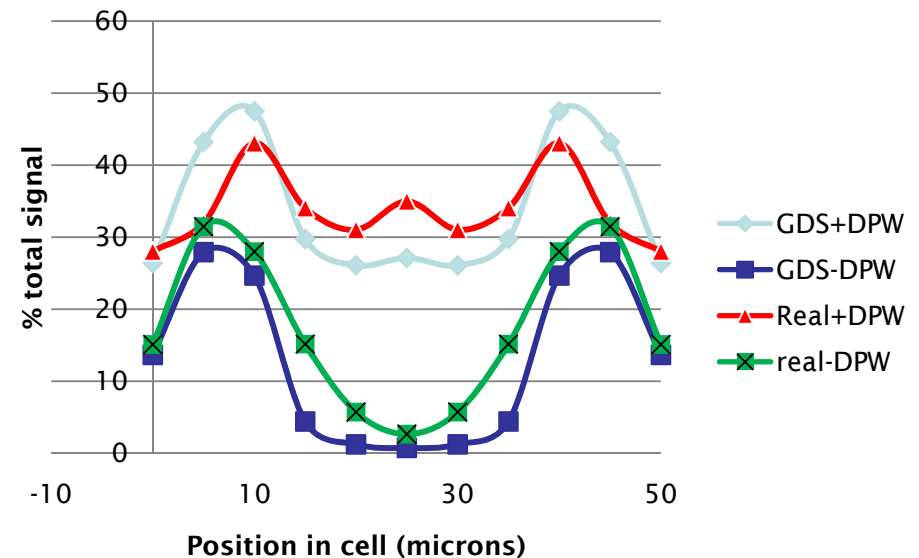
Single Pixel in Array: Laser Stimulus

- Amplitude results
 - With/without deep pwell
 - Compare
 - Simulations “GDS”
 - Measurements “Real”

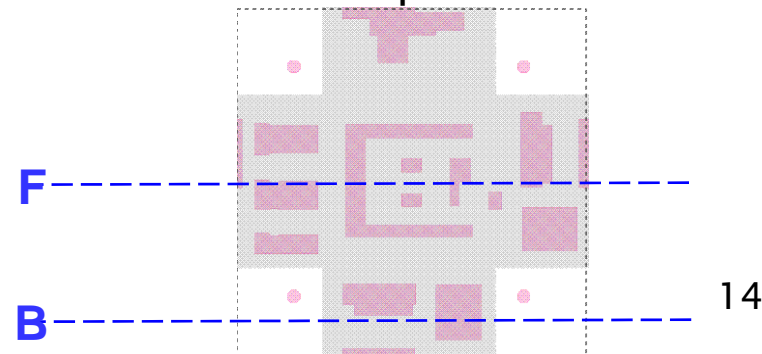
Profile F; through cell



Profile B; through cell

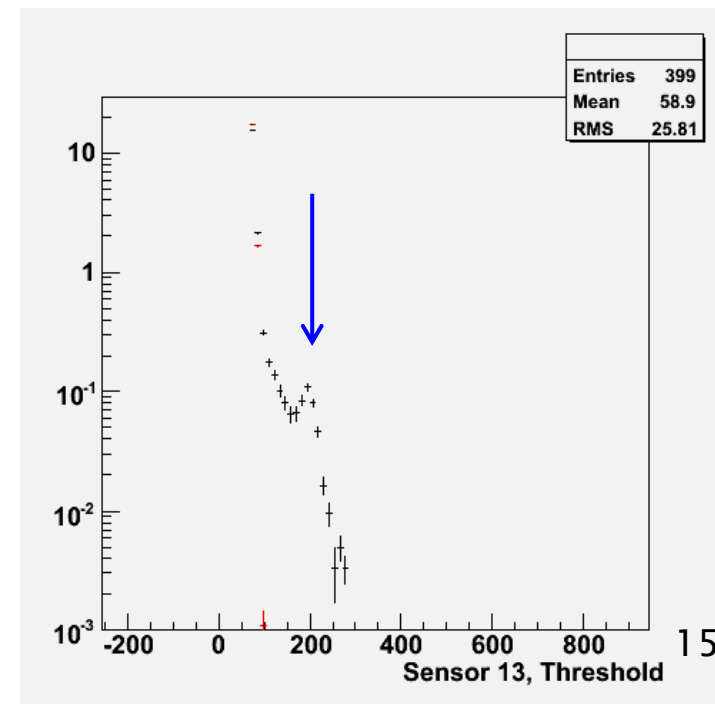
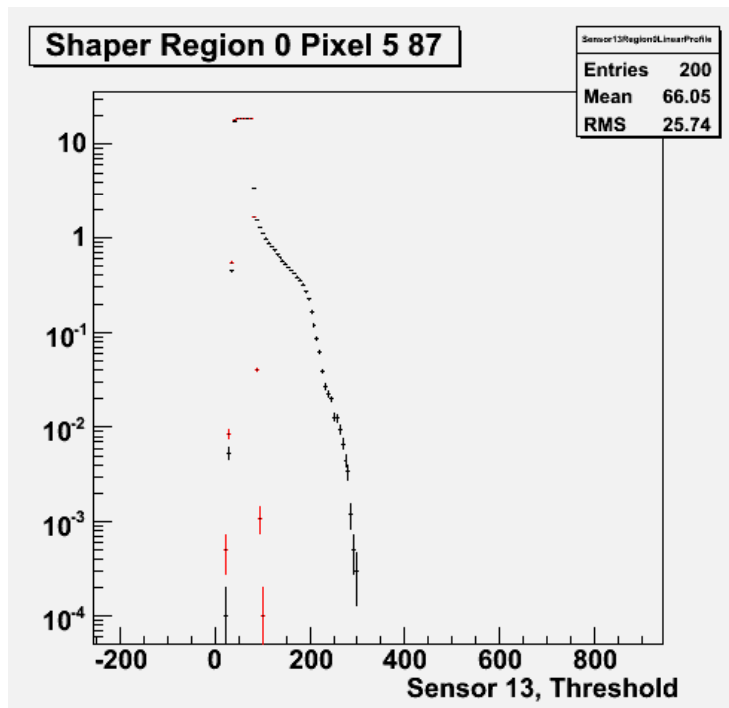


Pixel profiles



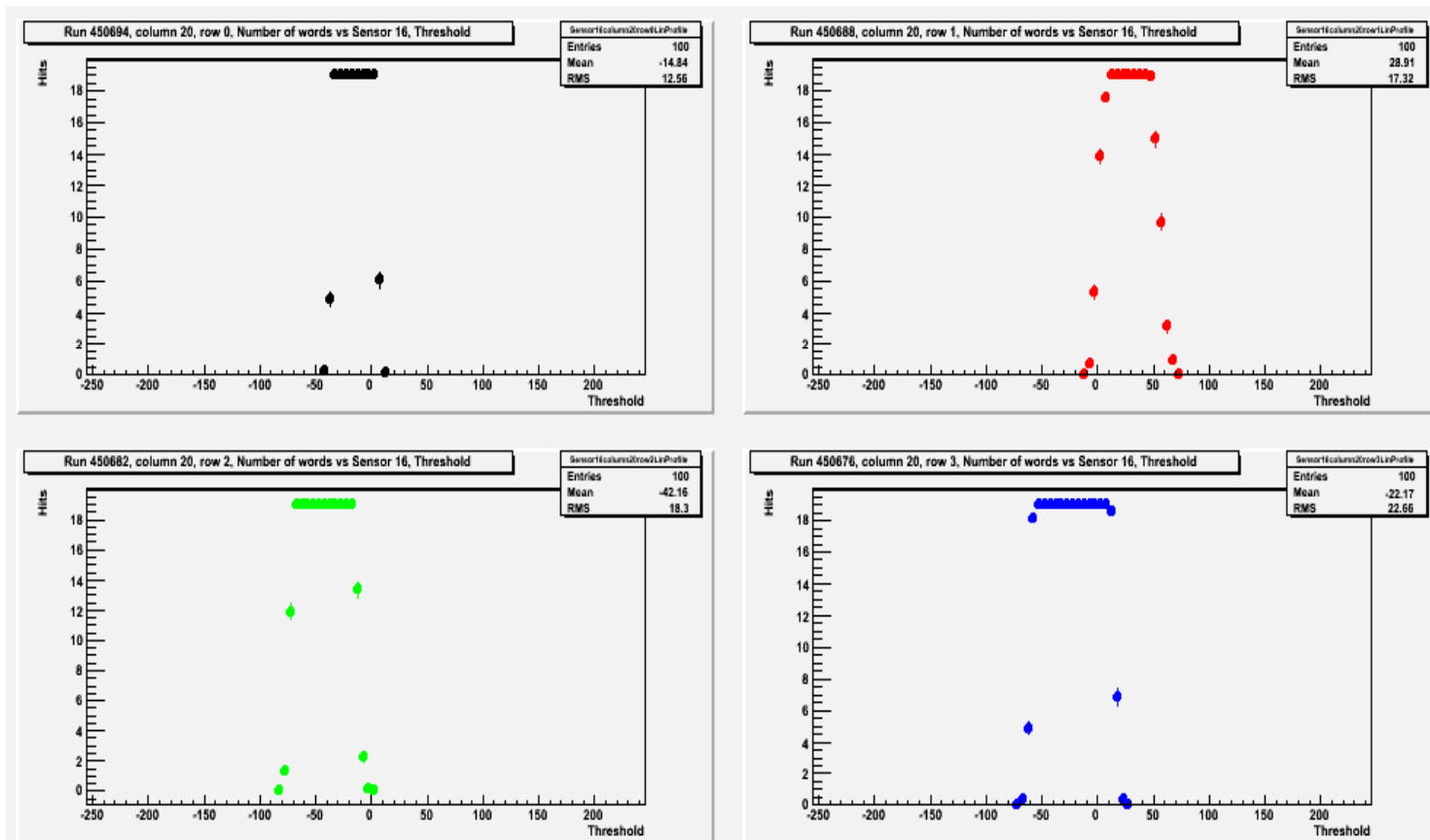
Single Pixel in Array: ^{55}Fe Source

- ^{55}Fe gives **5.9keV** photon
 - Deposits all energy in “point” in silicon; **1640e⁻**
 - Sometimes will deposit maximum energy in a single diode and no charge will diffuse
→ absolute calibration!
- Binary readout from pixel array
 - Need to differentiate distribution to get signal peak in threshold units (TU)
 - Differential approximation

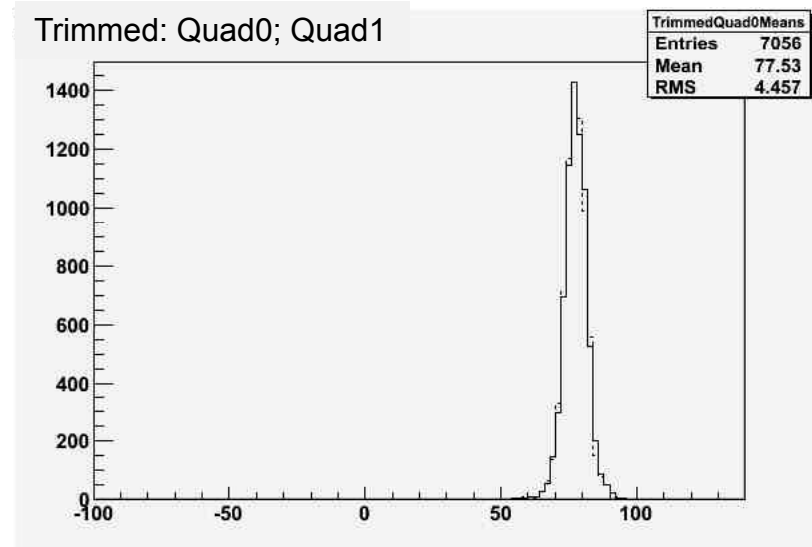
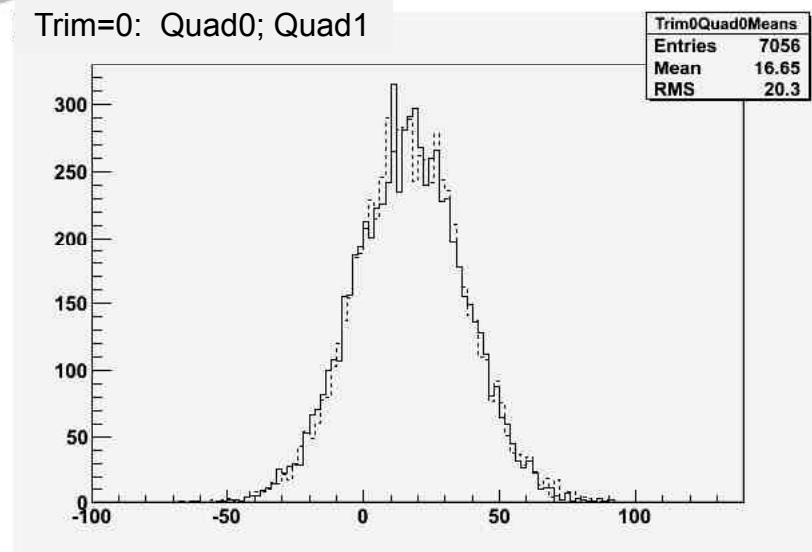


Array of PreShape Pixels: Pedestals

- Threshold scan of individual pixels
 - Low resolution (for speed)
- Note differing threshold scans of noise



Array of PreShape Pixels: Pedestals



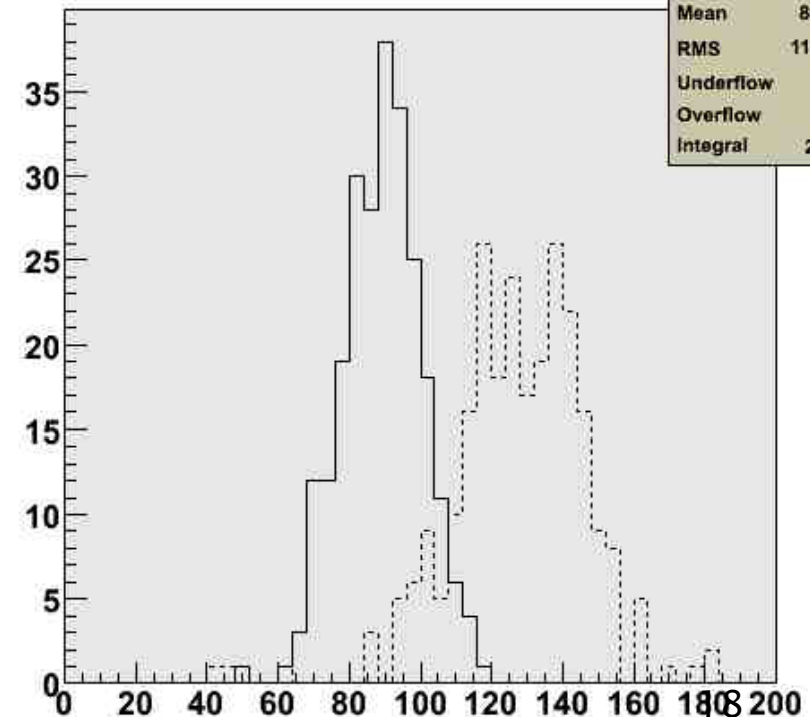
- ← • Plot the distribution of pedestals
 - Mean
- Calculate necessary trim adjustment
- Per-pixel trim file
 - uni-directional adjustment
- Re-scan pixels individually with trims
- ← • Re-plot the distribution of pedestals

Array of PreShape Pixels: Gains

- Use laser to inject fixed-intensity signal into many pixels
- Relative position should be equivalent for each pixel scanned
- Adjust/trim for known pixel pedestals

- Gain uniform to 12%
- Quad1 ~40% more gain than Quad0
- Quad1 ~20% better S/N than Quad0

Signal Quad0



Immediate Future

- Characterisation of v1.0 is still ongoing
 - Automated laser tests
 - Cosmics stack
- Version 1.1 due back late September
 - One pixel variant selected (preShape quad1)
 - Upgrade trim adjustment from 4bits to 6bits
 - Compatible format: size, pins, pcb, daq etc.
 - Minor bugs fixed
 - Additional test pixels & devices
- Version 1.1 Full Characterisation
 - (...as for v1.0)
 - Beam test early 2009

Conclusions

- First Sensor
 - Successful operation of highly complex pixels
 - See ^{55}Fe radioactive source
 - See laser injection of charge
 - See beam particles (albeit with low efficiency at the time)
 - Proved viability of the Deep P-Well for applying MAPS to particle physics
 - Selected a preferred pixel design to take forward
- Revised Sensor
 - Uniform array of improved pixels
 - Full characterisation ready to go!
- Long Term
 - Larger format sensors to prove Digital ECAL in a stack!